

AMENDMENT TO THE CLAIMS

The following claim listing replaces all prior listings and versions of the claims:

LISTING OF CLAIMS

1. (Currently Amended) An electret condenser, comprising:
a first electrode;
a second electrode;
a first insulating film which is formed between the first electrode and the second electrode and is electretized; and
a second insulating film formed so as to cover upper, lower and side surfaces of the first insulating film,
wherein the first insulating film covered with the second insulating film is formed on the second electrode,
the second electrode, the first insulating film, and the second insulating film compose a vibrating film, and
the second insulating film is formed to be in contact with at least one of the upper, side and lower surfaces of the first insulating film.
2. (Previously Presented) A method for manufacturing the electret condenser of Claim 1,
wherein the first insulating film is a silicon dioxide film grown in an atmosphere at a temperature in a range between 500 °C and 800 °C, both inclusive.

3. (Previously Presented) A method for manufacturing the electret condenser of Claim 1,

wherein the second insulating film is a silicon nitride film grown in an atmosphere at a temperature in the range between 600 °C and 800 °C, both inclusive

4. (Cancelled)

5. (Currently Amended) The electret condenser of Claim [[4]] 1,
wherein a shape in plan of the first insulating film is smaller than a shape in plan of the vibrating film, and

the first insulating film is arranged at a central part of the vibrating film.

6. (Currently Amended) An electret condenser, comprising:
a first electrode;
a second electrode; and
a first insulating film which is formed between the first electrode and the second electrode and is electretized,
wherein a lower surface of the first insulating film is covered with the second electrode and upper and side surfaces of the first insulating film are covered with a second insulating film,
the second electrode, the first insulating film, and the second insulating film compose a vibrating film, and

the second insulating film is formed to be in contact with at least one of the upper and side surfaces of the first insulating film.

7. (Previously Presented) A method for manufacturing the electret condenser of Claim 6,

wherein the first insulating film is a silicon dioxide film grown in an atmosphere at a temperature in a range between 500 °C and 800 °C, both inclusive.

8. (Previously Presented) A method for manufacturing the electret condenser of Claim 6,

wherein the second insulating film is a silicon nitride film grown in an atmosphere at a temperature in the range between 600 °C and 800 °C, both inclusive.

9. (Cancelled)

10. (Currently Amended) The electret condenser of Claim [[9]] 6,

wherein a shape in plan of the first insulating film is smaller than a shape in plan of the vibrating film, and

the first insulating film is arranged at a central part of the vibrating film.

11. (New) The electret condenser of claim 1,

wherein the second insulating film is formed to be in contact with the upper and side surfaces of the first insulating film.

12. (New) The electret condenser of claim 1,
wherein the second insulating film is formed to be in contact with the upper, side and lower surfaces of the first insulating film.

13. (New) The electret condenser of claim 1,
wherein the first electrode is included in a fixed film.

14. (New) The electret condenser of claim 6,
wherein the second insulating film is formed to be in contact with the upper and side surfaces of the first insulating film.

15. (New) The electret condenser of claim 6,
wherein the second insulating film is formed to be in contact with the upper and side surfaces of the first insulating film, and
the second electrode is formed to be in contact with the lower surface of the first insulating film.

16. (New) The electret condenser of claim 6,
wherein the first electrode is included in a fixed film.

17. (New) An electret condenser, comprising:
a first electrode;

a second electrode;

a first insulating film which is formed between the first electrode and the second electrode and is electretized; and

a second insulating film formed so as to be in contact with at least one of upper, lower and side surfaces of the first insulating film.

18. (New) The electret condenser of claim 17,

wherein the first insulating film is formed on the second electrode.

19. (New) The electret condenser of claim 17,

wherein at least one of the first electrode and the second electrode is included in a vibrating film.

20. (New) The electret condenser of claim 17,

wherein the second insulating film is formed to be in contact with the upper and side surfaces of the first insulating film.

21. (New) The electret condenser of claim 17,

wherein the second insulating film is formed to be in contact with the upper, side and lower surfaces of the first insulating film.

22. (New) The electret condenser of claim 17,

wherein at least one of the first electrode and the second electrode is included in a fixed film.

23. (New) The electret condenser of claim 17,
wherein the first insulating film is a silicon dioxide film.

24. (New) The electret condenser of claim 17,
wherein the second insulating film is a silicon nitride film.